

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A semiconductor device includes an N channel MOS transistor. The N channel MOS transistor includes a first P type buried layer that isolates an N epitaxial region ~~formed~~ on a P type substrate (P-SUB) from another N epitaxial region, a drain ~~formed~~ in an N well in the N epitaxial region, a source ~~formed~~ in a P well surrounding ~~side-faces~~ sides of the N well ~~so as to be separated from~~ isolate the N well, and a gate ~~formed~~ on ~~each~~ upper layer ~~portion~~ portions of the drain and the source. The MOS transistor also includes a second P type buried layer ~~formed below~~ between the N well and the P well ~~so as to be joined~~ and the substrate and contiguous to the P well, and an N buried layer ~~formed so as to be joined~~ contiguous to the P type buried layer and the P-SUB. The N epitaxial region, the P-SUB, and the first P type buried layer are connected to ground potential.